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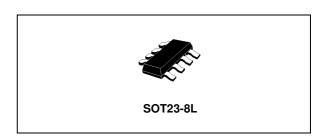


DUAL BILATERAL SWITCH

- HIGH SPEED:
 - $t_{PD} = 0.3$ ns (TYP.) at $V_{CC} = 5V$ $t_{PD} = 0.4$ ns (TYP.) at $V_{CC} = 3.3V$
- LOW POWER DISSIPATION: $I_{CC} = 1\mu A(MAX.)$ at $T_A = 25$ °C
- LOW "ON" RESISTANCE: R_{ON} =6.5 Ω (TYP.) AT V_{CC} = 5V $I_{I/O}$ = 1mA R_{ON} = 8.5 Ω (TYP.) AT V_{CC} = 3.3V $I_{I/O}$ = 1mA
- SINE WAVE DISTORTION: 0.04% AT V_{CC} = 3.3V f = 1KHz
- WIDE OPERATING RANGE: V_{CC} (OPR) = 2V TO 5.5V
- IMPROVED LATCH-UP IMMUNITY



The 74V2G66 is an advanced high-speed CMOS DUAL BILATERAL SWITCH fabricated in silicon gate C^2 MOS technology. It achieves high speed propagation delay and VERY LOW ON resistances while maintaining true CMOS low power consumption. This bilateral switch handles rail to rail analog and digital signals that may vary across the full power supply range (from GND to V_{CC}).

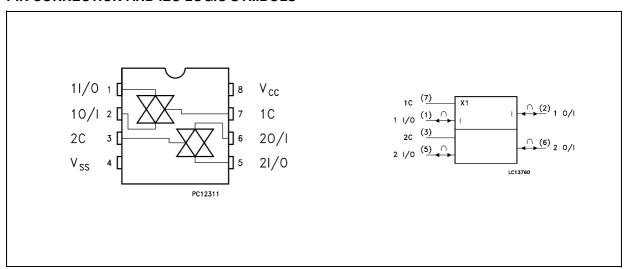


ORDER CODES

PACKAGE	T&R
SOT23-8L	74V2G66STR

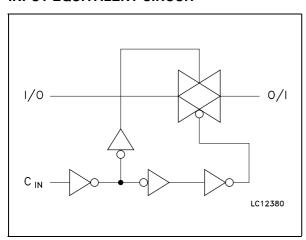
The C input is provided to control the switch and it's compatible with standard CMOS output; the switch is ON (port I/O is connected to Port O/I) when the C input is held high and OFF (high impedance state exists between the two ports) when C is held low. It can be used in many application as Battery Powered System, Test Equipment. It's available in the commercial and extended temperature range in SOT23-8L package. All inputs and output are equipped with protection circuits against static discharge, giving them ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



June 2003 1/9

INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 5	1I/O, 2I/O	Independent Input/Output
2, 6	10/I, 20/I	Independent Output/Input
7, 3	1C, 2C	Enable Input (Active HIGH)
4	GND	Ground (0V)
8	V _{CC}	Positive Supply Voltage

TRUTH TABLE

CONTROL	SWITCH FUNCTION
Н	ON
L	OFF *

^{*:} High Impedance State

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7.0	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _{IC}	DC Control Input Voltage	-0.5 to +7.0	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{IK}	DC Control Input Diode Current	- 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
Io	DC Output Current	± 50	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	2 to 5.5	V
V _I	Input Voltage	0 to V _{CC}	V
V _{IC}	Control Input Voltage	0 to 5.5	V
V _O	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 1) V _{CC} = 5.0V	0 to 20	ns/V

¹⁾ V_{IN} from 30% to 70% of V_{CC} on control pin

DC SPECIFICATIONS

		T	est Condition				Value				
Symbol	Symbol Parameter		V _{CC}		T _A = 25°C			85°C	-55 to	125°C	Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input	2.0		1.5			1.5		1.5		
	Voltage	2.7 to 5.5		0.7V _{CC}			0.7V _{CC}		0.7V _{CC}		V
V_{IL}	Low Level Input	2.0				0.5		0.5		0.5	
	Voltage	2.7 to 5.5				0.3V _{CC}		0.3V _{CC}		0.3V _{CC}	V
R _{ON}	ON Resistance	3.3 ^(*)	$V_{IC} = V_{IH}$		12.5	19		23		27	
		5.0 ^(**)	$V_{I/O} = V_{CC}$ to GND $I_{I/O} \le 1 \text{mA}$		7.5	10		12		14	Ω
R _{ON}	ON Resistance	3.3 ^(*)			8.5	10.5		12.5		15	
		5.0(**)	$V_{I/O} = V_{CC}$ or GND $I_{I/O} \le 1 \text{mA}$		6.5	8.5		10		12	Ω
l _{OFF}	Input/Output Leakage Current (SWITCH OFF)	5.5	$V_{OS} = V_{CC}$ to GND $V_{IS} = V_{CC}$ to GND $V_{IC} = V_{IL}$			±0.1		± 1		± 5	μΑ
I _{IZ}	Switch Input Leakage Current (SWITCH ON, OUTPUT OPEN)	5.5	$V_{OS} = V_{CC}$ to GND $V_{IC} = V_{IH}$			±0.1		± 1		± 5	μΑ
I _{IN}	Control Input Leakage Current	0 to 5.5	V _{IC} = 5.5V or GND			± 0.1		± 1.0		± 1.0	μΑ
I _{CC}	Quiescent Supply Current	5.5	$V_I = V_{CC}$ or GND			1		10		20	μΑ

^(*) Voltage range is $3.3V \pm 0.3V$ (**) Voltage range is $5V \pm 0.5V$

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 pF$, Input $t_r = t_f = 3 ns$)

		Test Condition		Value							
Symbol	Parameter	ν _{cc}		Т	A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		V _{CC} (V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{PD}	Delay Time	3.3 ^(*)	$t_r = t_f = 6ns$		0.4	0.8		1.2		2.4	20
		5.0 ^(**)	$t_r = t_f = 0.05$		0.3	0.6		1.0		2.0	ns
t _{PLZ}	Output Disable	3.3(*)	$R_1 = 500 \Omega$		5.0	7.5		9.0		10.0	nc
t _{PHZ}	Time	5.0 ^(**)	11[= 300 22		5.0	7.5		9.0		10.0	ns
t _{PZL}	Output Enable	3.3 ^(*)	$R_1 = 1 \text{ K}\Omega$		2.5	4.0		5.0		7.0	ne
t _{PZH}	Time	5.0 ^(**)	11[= 1 1/22		2.0	4.0		5.0		7.0	ns

^(*) Voltage range is $3.3V \pm 0.3V$ (**) Voltage range is $5.0V \pm 0.5V$

CAPACITIVE CHARACTERISTICS

		1	est Condition		Value						
Symbol Parameter	v _{cc}	V _{CC}	T _A = 25°C			-40 to	85°C	-55 to 125°C		Unit	
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C _{IN}	Input Capacitance				3	10		10		10	pF
C _{I/O}	Output Capacitance				10						pF
C _{PD}	Power Dissipation	3.3			2.5						
	Capacitance (note 1)	5.0			3						pF

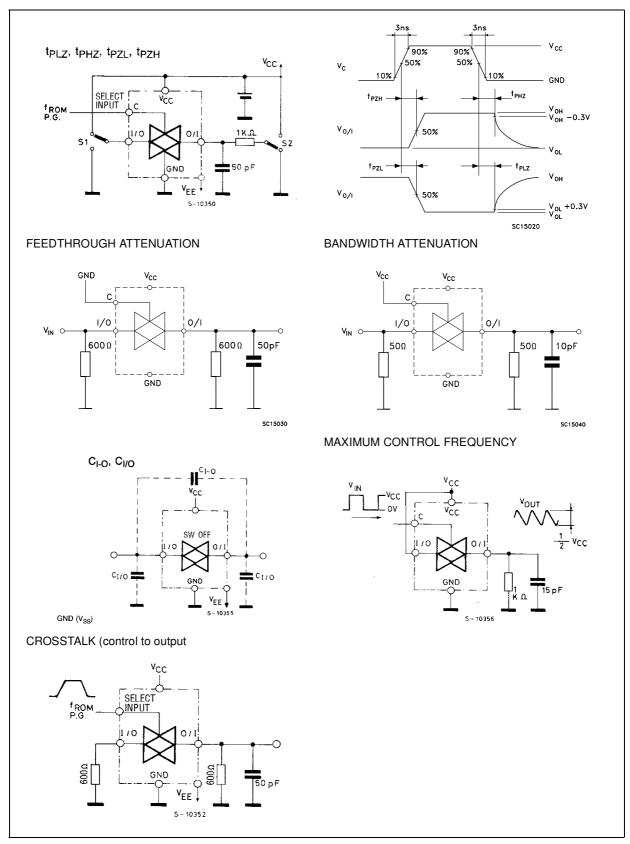
¹⁾ C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/4$

ANALOG SWITCH CHARACTERISTICS (GND = 0V; $T_A = 25^{\circ}C$)

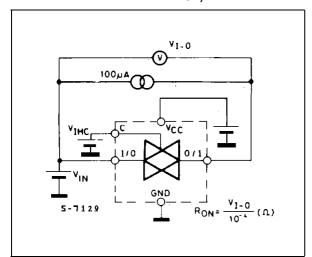
			Test Condition				
Symbol	Parameter	V _{CC} (V)	V _{IN} (V _{p-p})		Тур.	Unit	
	Sine Wave	3.3 ^(*)	2.75	$f_{IN} = 1 \text{ KHz R}_{I} = 10 \text{ K}\Omega, C_{I} = 50 \text{ pF}$	0.04	%	
	Distortion (THD)	5.0 ^(**)	4	$I_{IN} = I \ \text{KHZ } N_L = I U \ \text{K2Z}, \ U_L = 30 \ \text{pr}$		/0	
f _{MAX}	Frequency	3.3 ^(*)		Adjust f_{IN} voltage to obtain 0 dBm at V_{OS} .	150		
	Response (Switch ON)	5.0 ^(**)		Increase f_{IN} Frequency until dB meter reads -3dB $R_L = 50\Omega$, $C_L = 10$ pF	180	MHz	
	Feed through	3.3 ^(*)		V _{IN} is centered at V _{CC} /2	-60		
	Attenuation (Switch OFF)	5.0(**)		Adjust f_{IN} Voltage to obtained 0dBm at V_{IS} $R_L = 600\Omega$, $C_L = 50$ pF, $f_{IN} = 1$ KHz sine wave	-60	dB	
	Crosstalk (Control	3.3 ^(*)		$R_L = 600\Omega$, $C_L = 50$ pF, $f_{IN} = 1$ KHz square wave	60	\/	
	Input to Signal Output)	5.0 ^(**)		$t_r = t_f = 6$ ns	60	mV	

^(*) Voltage range is 3.3V ± 0.3V (**) Voltage range is 5.0V ± 0.5V

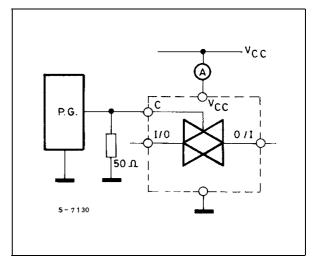
SWITCHING CARACTERISTICS TEST CIRCUIT



CHANNEL RESISTANCE (R_{ON)}

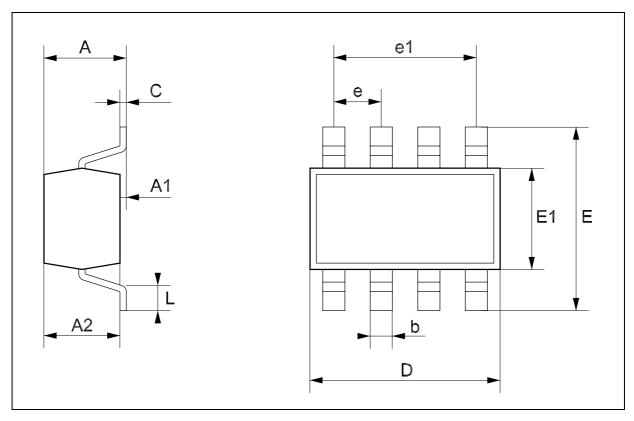


I_{CC} (Opr.)

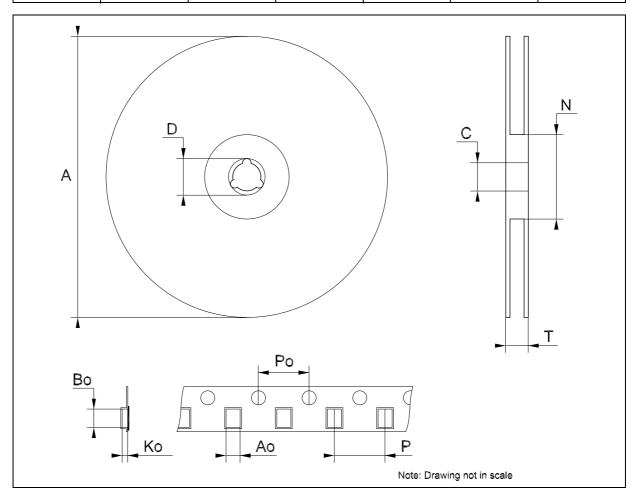


SOT23-8L MECHANICAL DATA

DIM		mm.		mils				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
А	0.90		1.45	35.4		57.1		
A1	0.00		0.15	0.0		5.9		
A2	0.90		1.30	35.4		51.2		
b	0.22		0.38	8.6		14.9		
С	0.09		0.20	3.5		7.8		
D	2.80		3.00	110.2		118.1		
E	2.60		3.00	102.3		118.1		
E1	1.50		1.75	59.0		68.8		
е	0	.65			25.6			
e1		1.95			76.7			
L	0.35		0.55	13.7		21.6		



DIM		mm.		inch				
DIM.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.		
Α			180			7.086		
С	12.8	13.0	13.2	0.504	0.512	0.519		
D	20.2			0.795				
N	60			2.362				
Т			14.4			0.567		
Ao	3.13	3.23	3.33	0.123	0.127	0.131		
Во	3.07	3.17	3.27	0.120	0.124	0.128		
Ko	1.27	1.37	1.47	0.050	0.054	0.0.58		
Po	3.9	4.0	4.1	0.153	0.157	0.161		
Р	3.9	4.0	4.1	0.153	0.157	0.161		



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